



SHEET 1 of 6

INFORMATION DISCLOSURE  
CITATION

PTO-1449

Atty. Docket No.

NTI-029

Serial No.

10/005,615-9717

Applicant

CHANG, Fang-Cheng

Filing Date

11/7/2001

Group 2825

FC 1700

SEP 3 - 2002

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## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
W	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
	6,049,789	4/11/2000	Frison, et al.	705	59	6/24/1998
	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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NTI Use Only: 759; 150; 1

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	<b>Applicant</b> CHANG, Fang-Cheng	<b>RECEIVED</b> SEP 3 - 2002 TC 1700 Group 2825 NTI-029
	<b>Filing Date</b> 11/7/2001	

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
NS	JP 3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	GB 2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/14638 A1	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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	<b>Applicant</b> CHANG, Fang-Cheng	<b>Group</b> <del>2825</del> 2825
	<b>Filing Date</b> 11/7/2001	

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EXAMINER'S INITIALS	CITATION
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	<b>Filing Date</b> 11/7/2001		<b>Group</b> 2825 <del>4236</del>

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